2SA893, 2SA893A

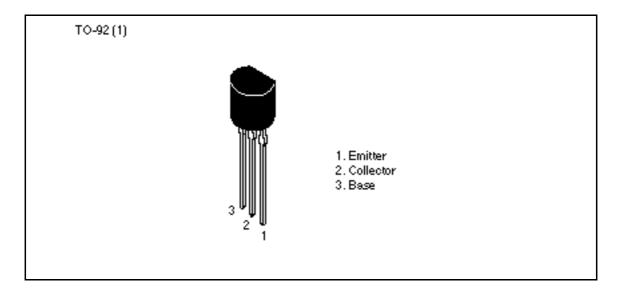
Silicon PNP Epitaxial

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Application

- Low frequency high voltage amplifier
- Complementary pair with 2SC1890/A

Outline





2SA893, 2SA893A

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SA893	2SA893A	Unit
Collector to base voltage	V_{CBO}	-90	-120	V
Collector to emitter voltage	V_{CEO}	-90	-120	V
Emitter to base voltage	V_{EBO}	- 5	- 5	V
Collector current	I _c	- 50	- 50	mA
Collector power dissipation	P _c	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

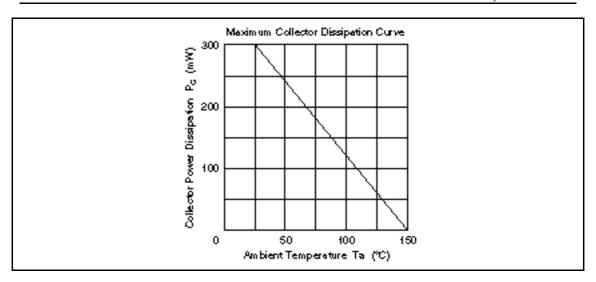
		2SA8	2SA893 2SA893A						
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	_	_	-120	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} =$
Collector cutoff current	I _{CBO}	_	_	-0.5	_	_	_	μΑ	$V_{CB} = -75 \text{ V}, I_{E} = 0$
		_	_	_	_	_	-0.5	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *1	250	_	800	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	-0.75	_	_	-0.75	V	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.5	_	_	-0.5	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}$
Gain bandwidth product	f _T	_	120	_	_	120	_	MHz	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob	_	1.8	_	_	1.8	_	pF	$V_{CB} = -25 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	2	10	_	2	10	dB	$V_{CE} = -6 \text{ V},$ $I_{C} = -50 \mu\text{A}$ $R_{g} = 50 \text{ k} \text{ , } f = 1 k\text{Hz}$

Note: 1. The 2SA893/A is grouped by h_{FE} as follows.

D E 250 to 500 400 to 800

See characteristic curves of 2SA872 and 2SA872A

2SA893, 2SA893A



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